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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



200V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON) MAX}$	$I_{D MAX}$ $T_A = +25^{\circ}C$
-200V	28Ω @ $V_{GS} = -10V$	-122mA

Description

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

- Active Clamping of Primary Side MOSFETs in 48V DC-DC Converters

Features and Benefits

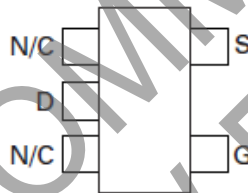
- High Voltage
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

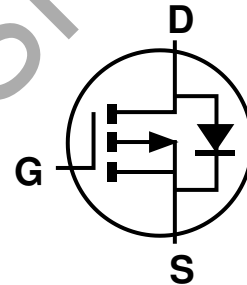
- Case: SOT25
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.016 grams (Approximate)



Top View



Pin Out - Top View



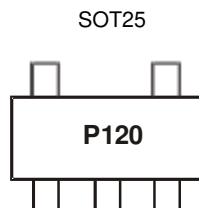
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMP2120E5TA	P120	7	8	3,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



P120 = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-200	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (V _{GS} = -10V; T _A = +25°C) (Note 5)	I _D	-122	mA
Pulsed Drain Current (Note 6)	I _{DM}	-0.7	A
Pulsed Source Current (Body Diode) (Note 6)	I _{SM}	-0.7	A

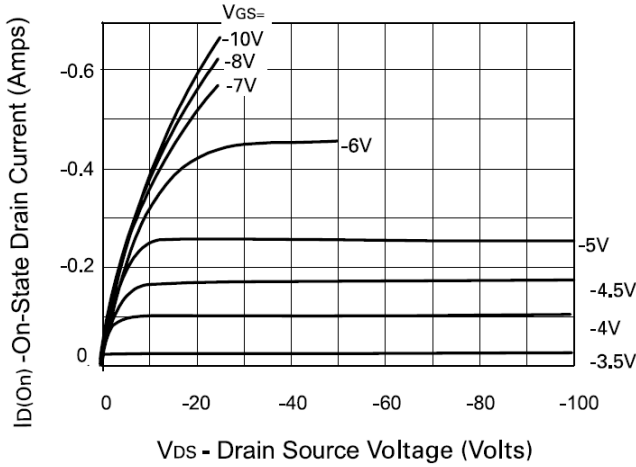
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5)	P _D	0.75	W
Linear Derating Factor		6	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	167	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

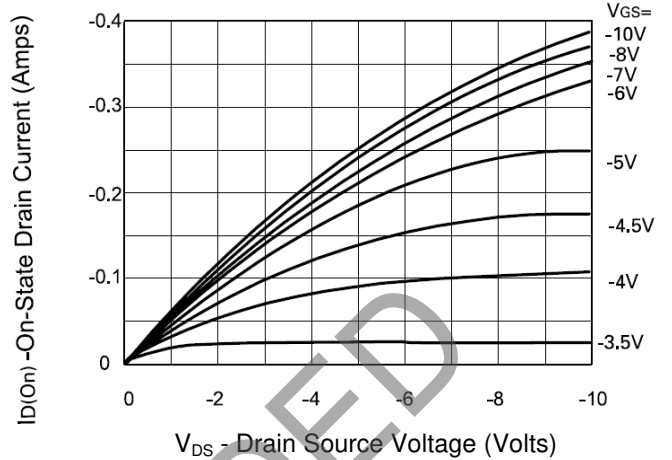
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-200	-	-	V	V _{GS} = 0V, I _D = -1mA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-10 -100	µA	V _{DS} = -200V, V _{GS} = 0V V _{DS} = -160V, V _{GS} = 0V, T _A = +125°C
Gate-Source Leakage	I _{GSS}	-	-	20	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	-1.5	-	-3.5	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance (Note 7)	R _{DS(ON)}	-	-	28	Ω	V _{GS} = -10V, I _D = -150mA
Forward Transconductance (Notes 7 & 8)	g _{fs}	50	-	-	ms	V _{DS} = -25V, I _D = -150mA
On-State Drain Current (Note 7)	I _{D(ON)}	-300	-	-	mA	V _{DS} = -25V, V _{GS} = -10V
DYNAMIC CHARACTERISTICS						
Input Capacitance (Note 8)	C _{iss}	-	-	100	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance (Note 8)	C _{oss}	-	-	25	pF	
Reverse Transfer Capacitance (Note 8)	C _{rss}	-	-	7	pF	
Turn-On Delay Time (Notes 8 & 9)	t _{D(ON)}	-	-	7	ns	V _{DD} = -25V, I _D = -150mA
Turn-On Rise Time (Notes 8 & 9)	t _R	-	-	15	ns	
Turn-Off Delay Time (Notes 8 & 9)	t _{D(OFF)}	-	-	12	ns	
Turn-Off Fall Time (Notes 8 & 9)	t _F	-	-	15	ns	

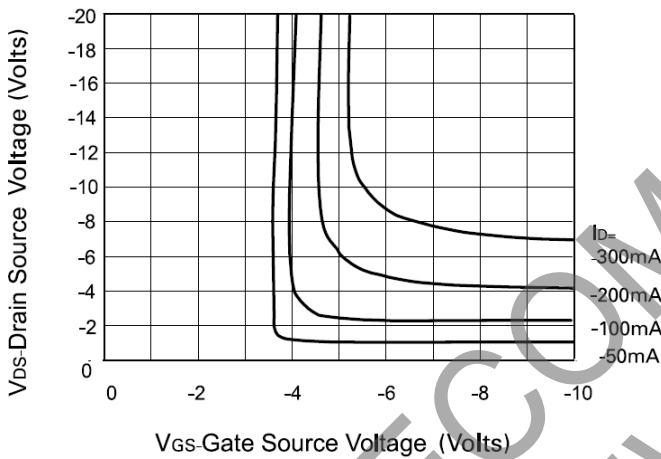
- Notes:
5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
 7. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.
 8. Sample test.
 9. Switching characteristics are independent of operating junction temperature.



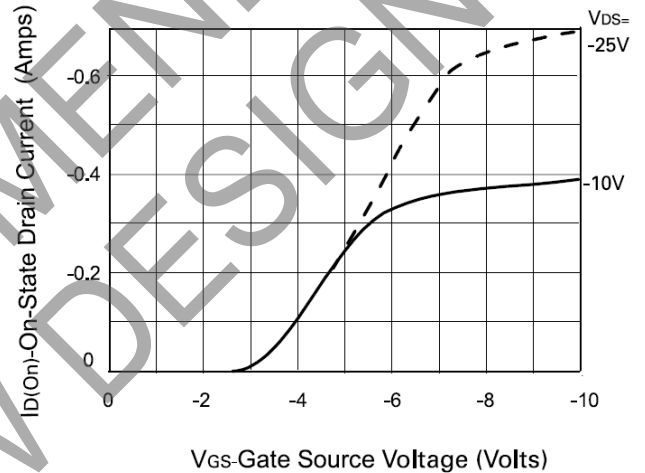
Output Characteristics



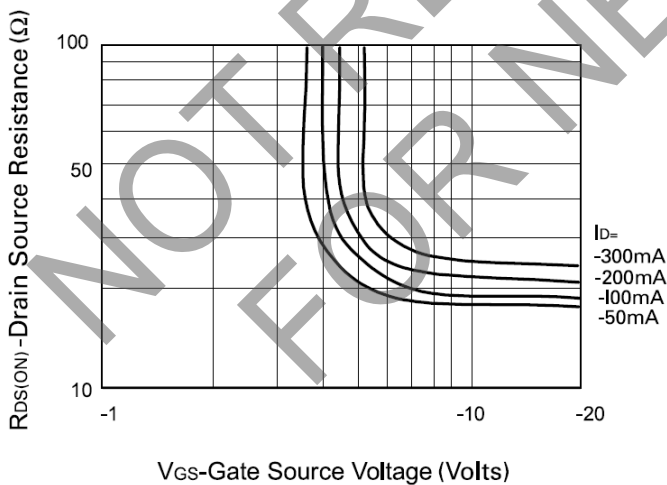
Saturation Characteristics



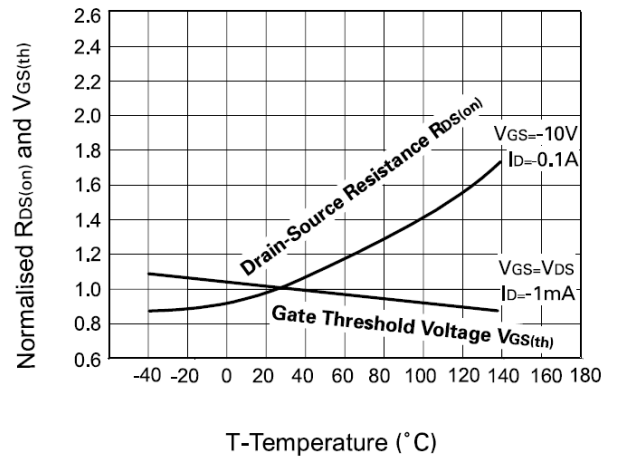
Voltage Saturation Characteristics



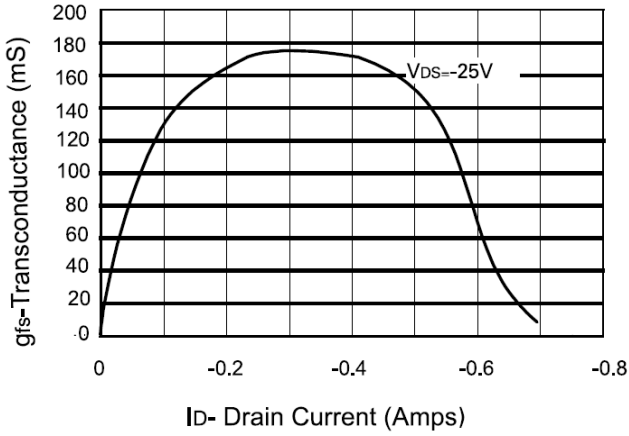
Transfer Characteristics



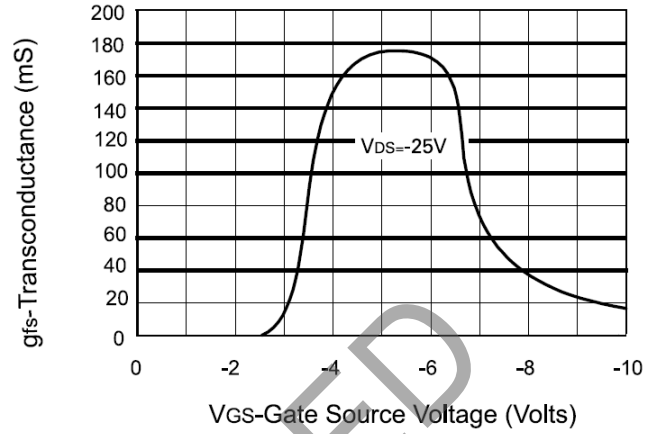
On-resistance vs gate-source voltage



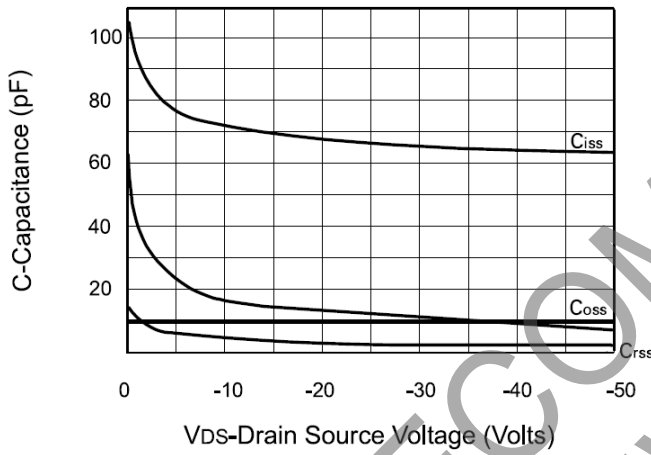
Normalised $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature



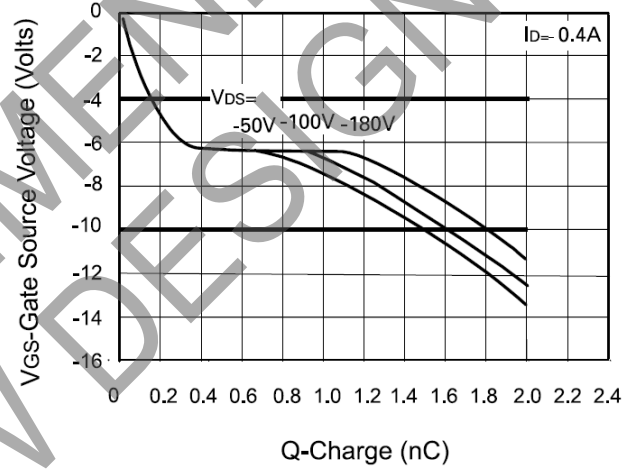
Transconductance v drain current



Transconductance v gate-source voltage



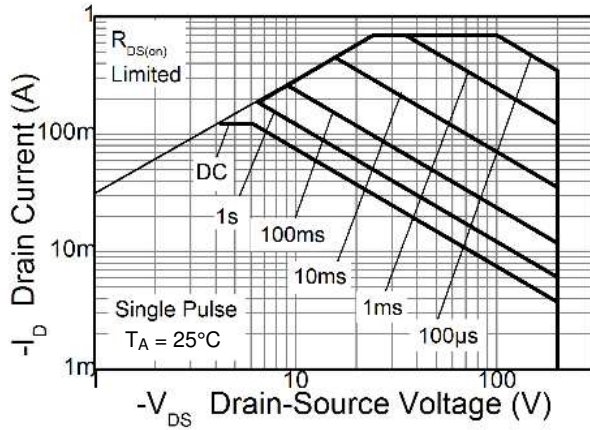
Capacitance v drain-source voltage



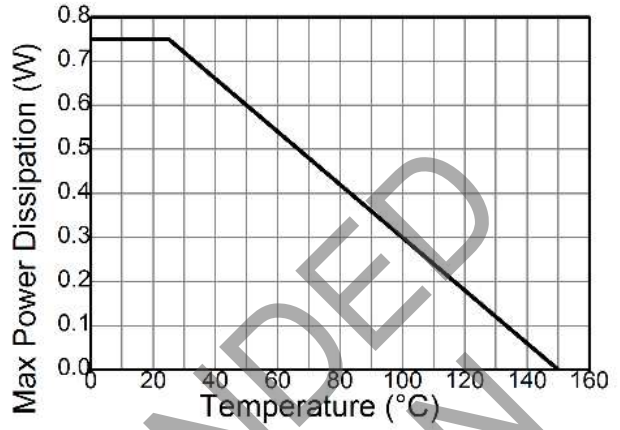
Gate charge v gate-source voltage

NOT RECOMMENDED FOR NEW DESIGN

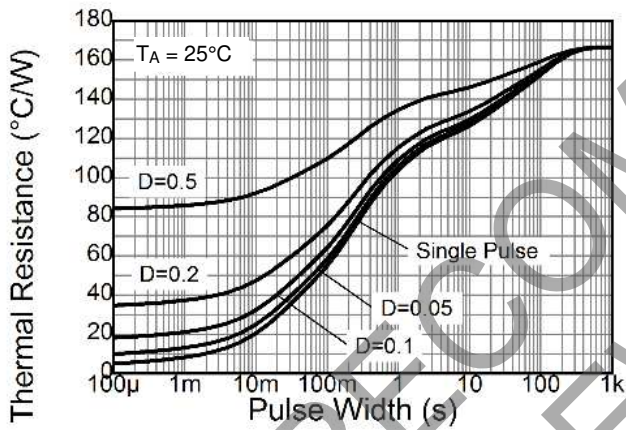
Thermal Characteristics



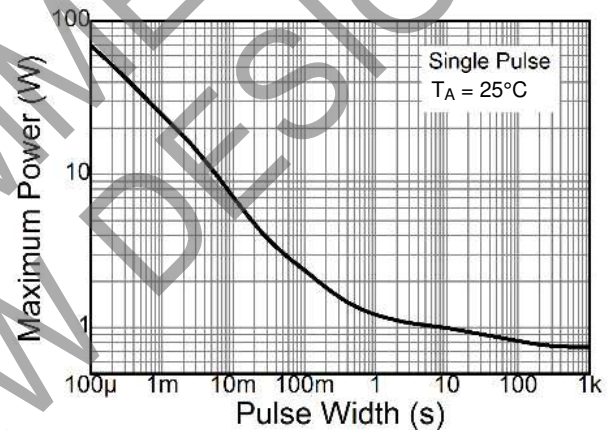
Safe Operating Area



Derating Curve



Transient Thermal Impedance

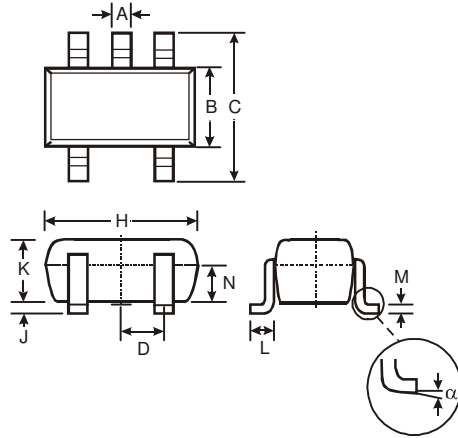


Pulse Power Dissipation

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT25

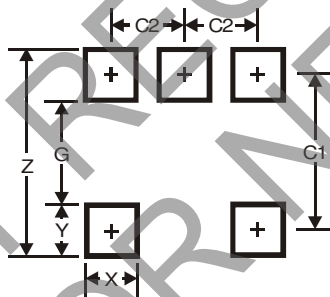


SOT25			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D			0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
N	0.70	0.80	0.75
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT25



Dimensions	SOT25
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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